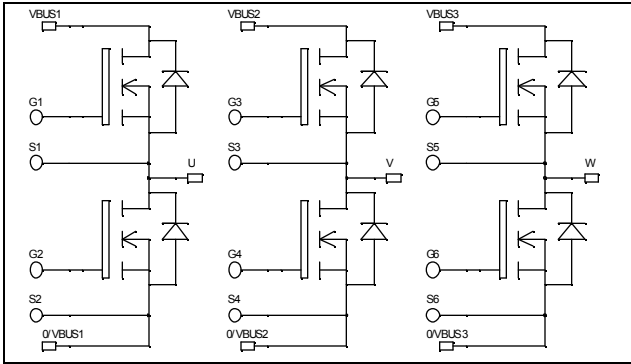


## Triple phase leg MOSFET Power Module

$V_{DSS} = 1000V$   
 $R_{DSon} = 350m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 22A \text{ @ } T_c = 25^\circ C$

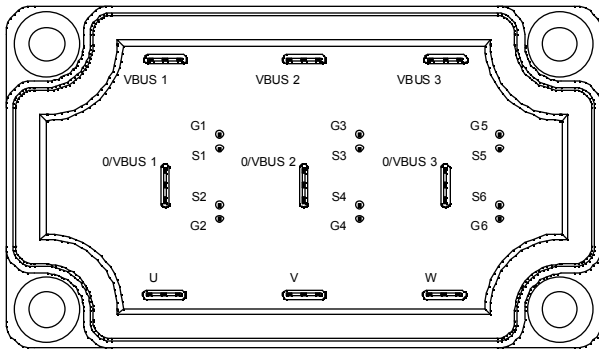


### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS 7<sup>®</sup> FREDFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration




### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1000	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	22
		$T_c = 80^\circ C$	17
$I_{DM}$	Pulsed Drain current	88	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	350	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	390
$I_{AR}$	Avalanche current (repetitive and non repetitive)	25	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{DSS}$	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1000			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$			250	$\mu A$
		$V_{GS} = 0V, V_{DS} = 800V$			1000	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 11A$			350	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5mA$	3		5	V
$I_{GSS}$	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 100$	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		5.2		nF
$C_{oss}$	Output Capacitance			0.88		
$C_{rss}$	Reverse Transfer Capacitance			0.16		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 500V$ $I_D = 22A$		186		nC
$Q_{gs}$	Gate - Source Charge			24		
$Q_{gd}$	Gate - Drain Charge			122		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V$ $V_{Bus} = 670V$ $I_D = 22A$ $R_G = 5\Omega$		18		ns
$T_r$	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			155		
$T_f$	Fall Time			40		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		900		$\mu J$
$E_{off}$	Turn-off Switching Energy ❷			623		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		1423		$\mu J$
$E_{off}$	Turn-off Switching Energy ❷			779		

## Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_S$	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			22	A	
		$T_c = 80^\circ\text{C}$			17		
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -22A$			1.3	V	
$dv/dt$	Peak Diode Recovery ❸				18	V/ns	
$t_{rr}$	Reverse Recovery Time	$I_S = -22A$ $V_R = 500V$ $di_S/dt = 100A/\mu s$	$T_j = 25^\circ\text{C}$			320	ns
			$T_j = 125^\circ\text{C}$			650	
$Q_{rr}$	Reverse Recovery Charge	$I_S = -22A$ $V_R = 500V$ $di_S/dt = 100A/\mu s$	$T_j = 25^\circ\text{C}$		3.6	$\mu C$	
			$T_j = 125^\circ\text{C}$		9.72		

❶  $E_{on}$  includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

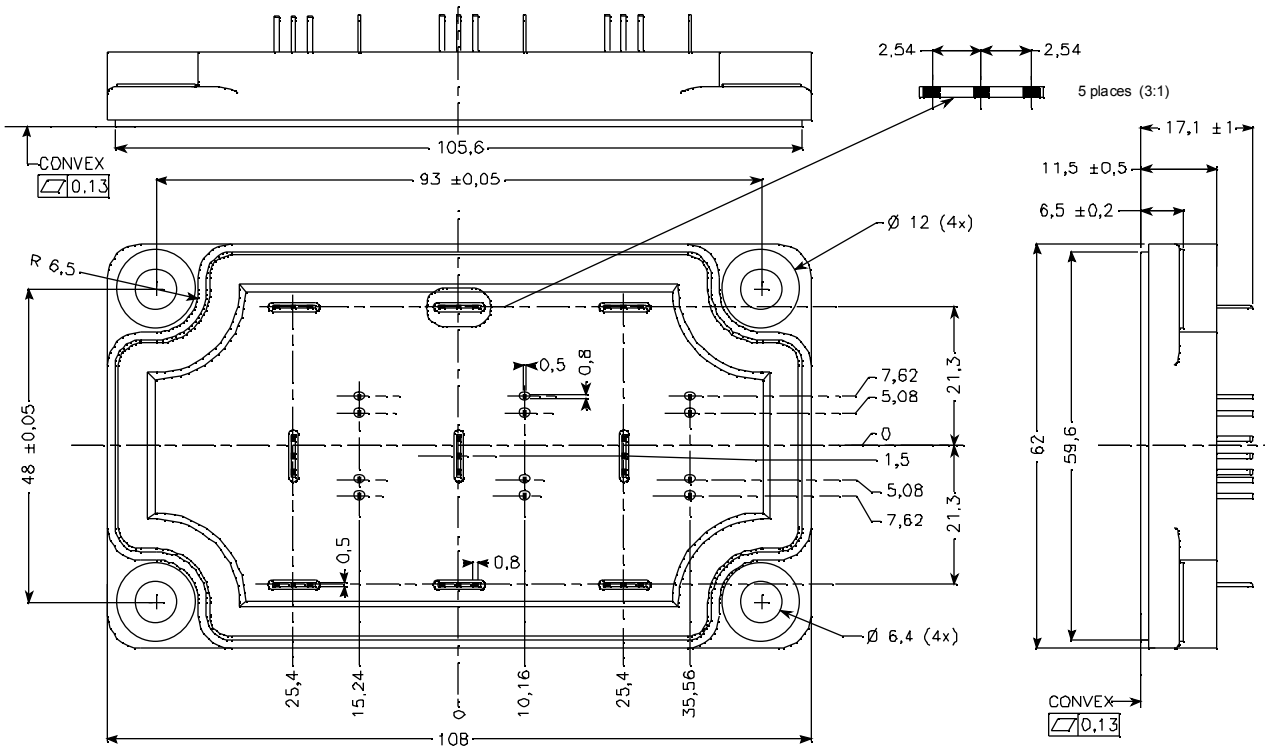
❸  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -22A \quad di/dt \leq 700A/\mu s \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

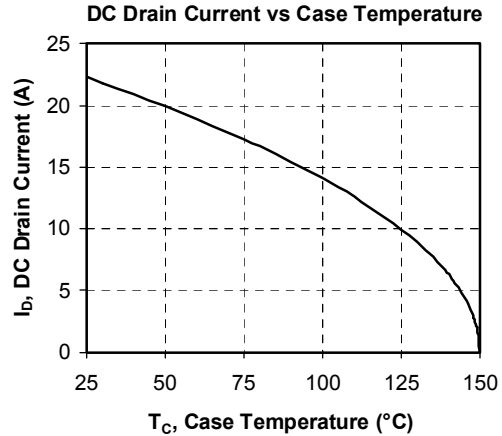
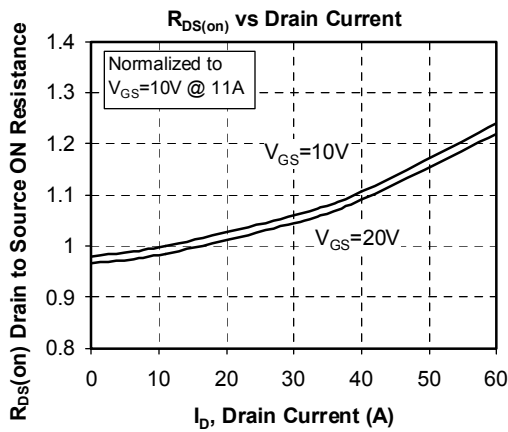
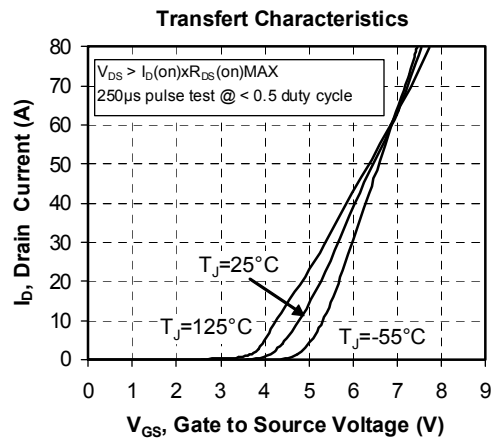
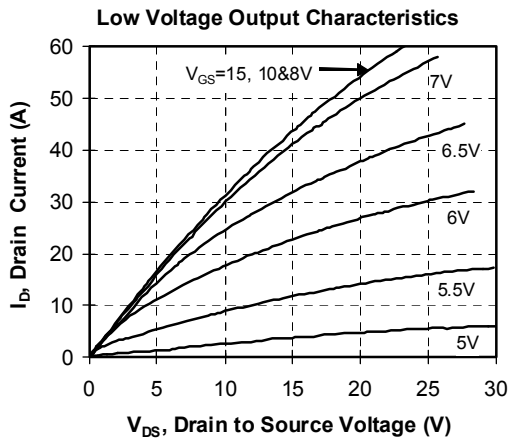
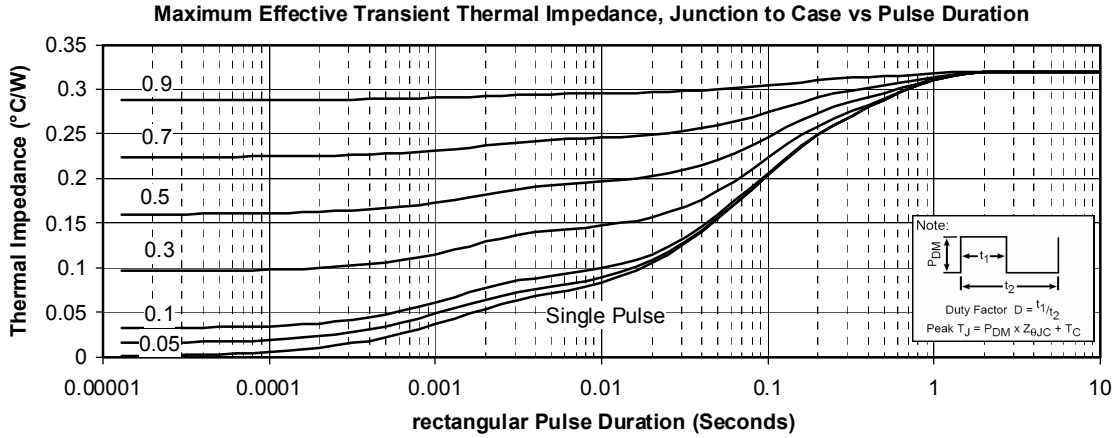
**Thermal and package characteristics**

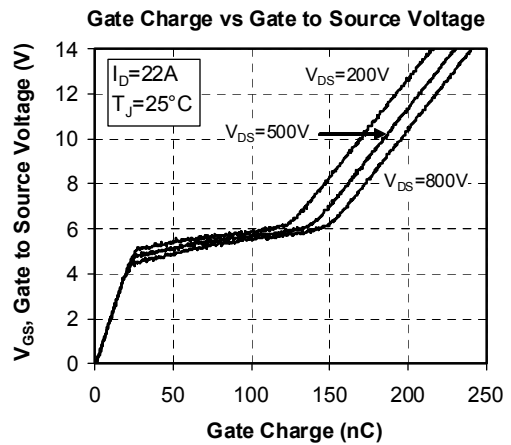
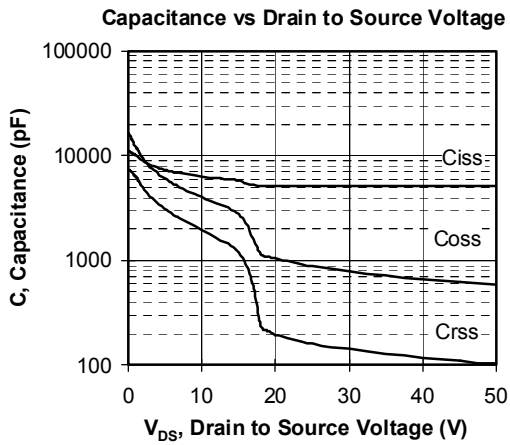
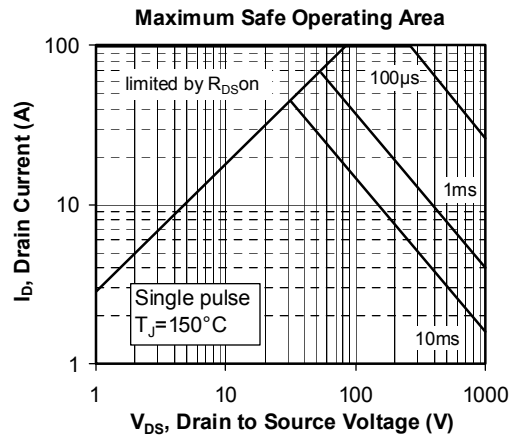
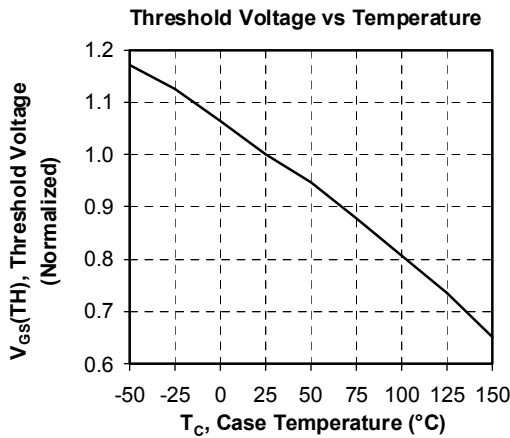
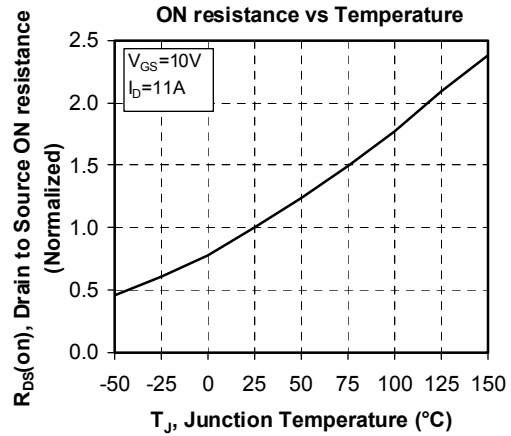
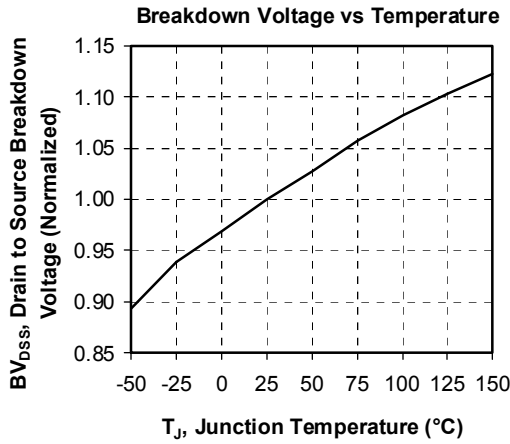
<i>Symbol</i>	<i>Characteristic</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R <sub>thJC</sub>	Junction to Case	IGBT			0.32	°C/W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz		2500			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

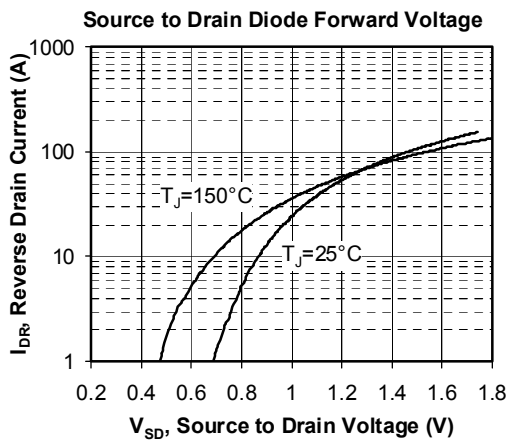
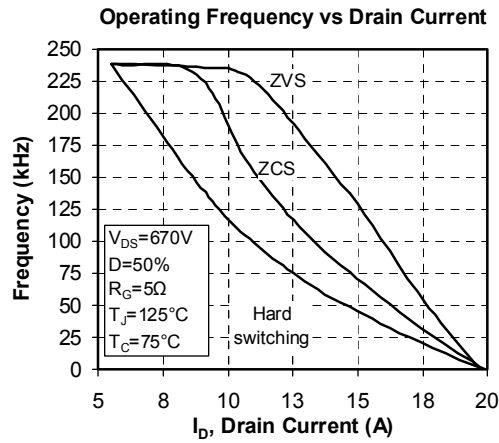
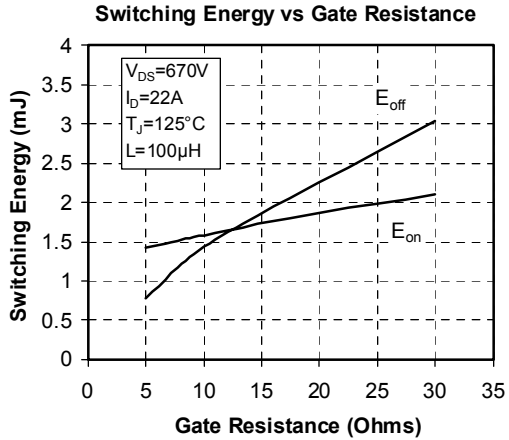
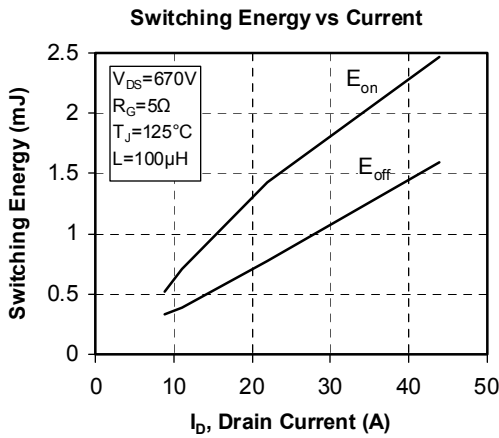
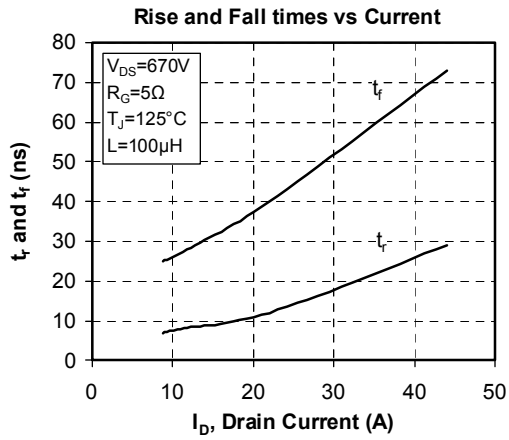
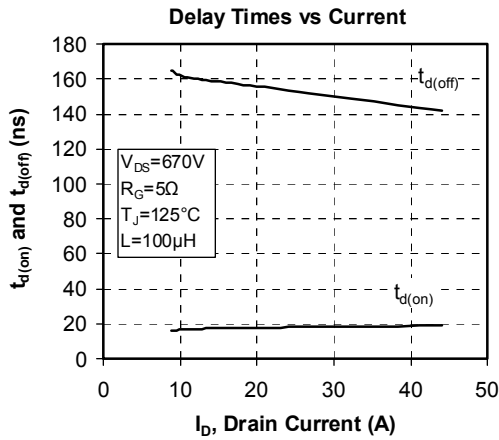
**Package outline**



**Typical Performance Curve**







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